

isc Silicon NPN Power Transistor

MJW21192

DESCRIPTION

- DC Current Gain
- High Area of Safe Operation

APPLICATIONS

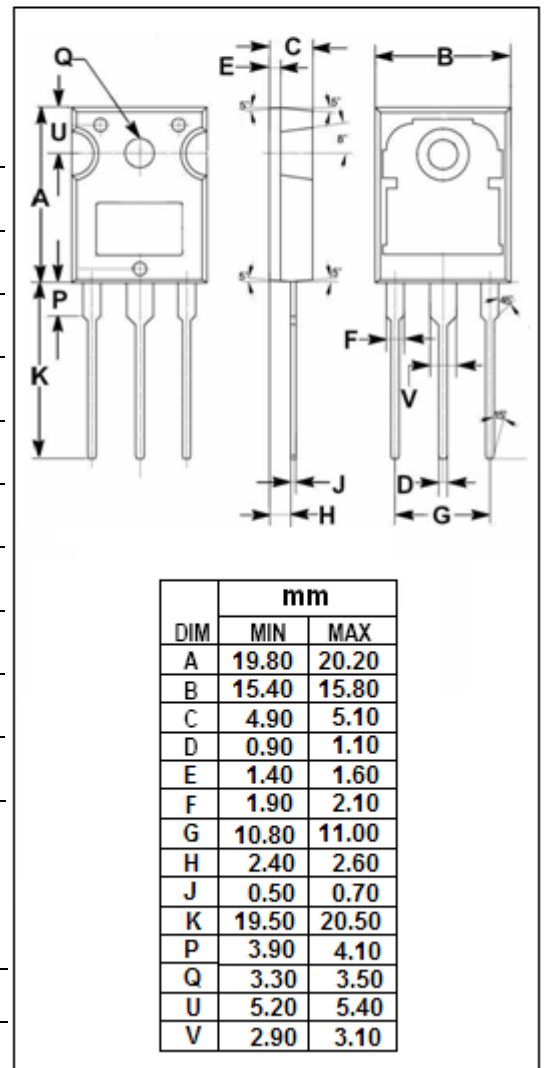
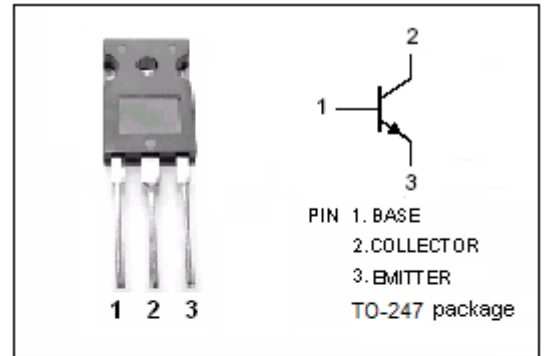
- Designed for power audio output, or high power drivers in audio amplifiers.

ABSOLUTE MAXIMUM RATINGS(Ta=25°C)

SYMBOL	PARAMETER	VALUE	UNIT
V <sub>CBO</sub>	Collector-Emitter Voltage	150	V
V <sub>CEO</sub>	Collector-Emitter Voltage	150	V
V <sub>EBO</sub>	Emitter-Base Voltage	5	V
I <sub>C</sub>	Collector Current-Continuous	8	A
I <sub>CM</sub>	Collector Current-Pulsed	16	A
I <sub>B</sub>	Base Current-Continuous	2	A
P <sub>D</sub>	Total Power Dissipation (T <sub>C</sub> =25°C)	100	W
T <sub>j</sub>	Junction Temperature	150	°C
T <sub>stg</sub>	Storage Temperature	-65~150	°C

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	VALUE	UNIT
R <sub>th j-c</sub>	ThermalResistance Junction To Case	0.65	°C/W



**isc Silicon NPN Power Transistor****MJW21192****ELECTRICAL CHARACTERISTICS****T<sub>j</sub>=25°C unless otherwise specified**

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>CEO(SUS)</sub>	Collector-Emitter Sustaining Voltage	I <sub>C</sub> =10mA; I <sub>B</sub> =0	150			V
V <sub>CE(sat)-1</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> =4A; I <sub>B</sub> =0.4A			1.0	V
V <sub>CE(sat)-2</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> =8A; I <sub>B</sub> =1.6A			2.0	V
V <sub>BE(on)</sub>	Base-Emitter On Voltage	I <sub>C</sub> =4A; V <sub>CE</sub> =2V			2	V
I <sub>CEs</sub>	Collector Cutoff Current	V <sub>CE</sub> =250V; I <sub>E</sub> =0			10	μ A
I <sub>EBO</sub>	Emitter Cutoff Current	V <sub>EB</sub> =5V; I <sub>C</sub> =0			10	μ A
h <sub>FE-1</sub>	DC Current Gain	I <sub>C</sub> =4A; V <sub>CE</sub> =2V	15		100	
h <sub>FE-2</sub>	DC Current Gain	I <sub>C</sub> =8A; V <sub>CE</sub> =2V	5			
f <sub>T</sub>	Current Gain-Bandwidth Product	I <sub>C</sub> =1A; V <sub>CE</sub> =10V; f <sub>test</sub> =1MHz	4			MHz